Revision. 3

MOS FET

Unit: mm

#### FK8V03020L

## **Panasonic**

## FK8V03020L

#### Silicon N-channel MOS FET

For lithium-ion secondary battery protection circuit

#### ■ Features

- · Low drain-source On-state Resistance RDS(on) typ =  $5.4 \text{ m}\Omega$  (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 3B

Established: 2011-06-03

: 2013-10-15

Revised

#### ■ Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

0. 16 (0.81)0.65 5. Drain 1. Source 2. Source 6. Drain 3. Source 7. Drain 8. Drain 4. Gate WMini8-F1 Panasonic JEITA SC-115 Code

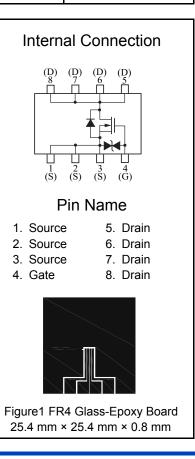
Absolute Maximum Rating	s Ta = 25 °	С
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Parameter	Symbol	Rating	Unit	
Drain-source Voltage	VDS	33	V	
Gate-source Voltage	VGS	±20	V	
Drain Current (Steady State) *1	ID	14		
Drain Current (t = 10 s) *1	טו	18	,	
Drain Current (Pulsed) *1,*2	IDp	56	Α	
Source Current (Pulsed)	ISp	14		
(Body Diode) *1,*2	(BD)	14		
Total Power Dissipation (Steady State) *1	PD	1	W	
Total Power Dissipation (t = 10 s) *1	FD	1.6	VV	
Channel Temperature	Tch	150	°C	
Operating Ambient Temperature	Topr	-40 to +85	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	
Avalanche Current *3	lar	60	Α	

Note: \*1 Device mounted on a glass-epoxy board (See Figure 1)

\*2 Pulse test: Ensure that the channel temperature does not exceed 150°C

\*3 Conditions: VDS = 24 V, VGS = 10 V, L = 10  $\mu$ H



Doc No. TT4-EA-13637 Revision. 3

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#### ■ Electrical Characteristics Ta = 25°C ± 3°C

#### Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			1	μΑ
Gate-source Leakage Current	IGSS	$VGS = \pm 16 \text{ V}, VDS = 0 \text{ V}$			±10	μΑ
Gate-source Threshold Voltage		ID = 2.2 mA, VDS = 10 V	1.0		3.0	V
Drain-source On-state Resistance *1	RDS(on)1	ID = 7A, VGS = 10 V		3.6	4.6	mΩ
	RDS(on)2	ID = 7A, VGS = 4.5 V		5.4	9.8	

#### **Dynamic Characteristics**

Input Capacitance	Ciss	VDS - 10 V VCS - 0 V	1500	
Output Capacitance	Coss	VDS = 10 V, VGS = 0 V f = 1 MHz	300	pF
Reverse Transfer Capacitance	Crss	1 = 1 1011 12	200	
Turn-on Delay Time *2	td(on)	VDD = 15 V, VGS = 0 to 10 V	10	
Rise Time *2	tr	ID = 7 A	5	ns
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V	200	115
Fall Time *2	tf	ID = 7 A	150	
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V,	14	
Gate-source Charge	Qgs	ID = 14 A	4	nC
Gate-drain Charge	Qgd	]   = 14 A	6	

Body Diode Characteristic					
Diode Forward Voltage *1	VSD	IS = 7 A, VGS = 0 V	0.8	1.2	V

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

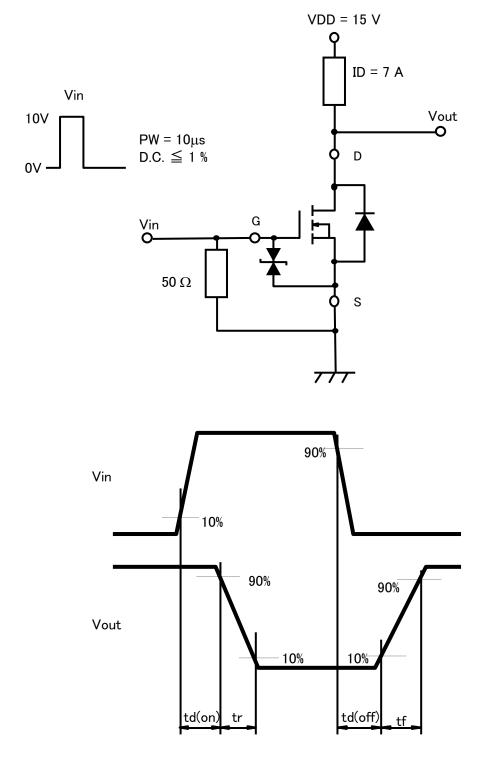
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Established: 2011-06-03 : 2013-10-15 Revised

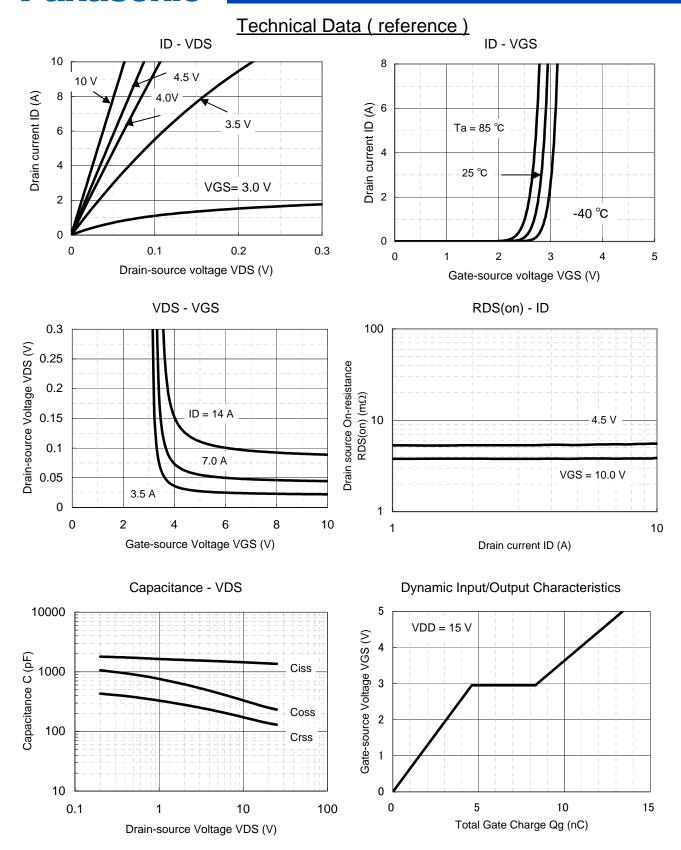
<sup>2. \*1</sup> Pulse test: Ensure that the channel temperature does not exceed 150°C

<sup>\*2</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

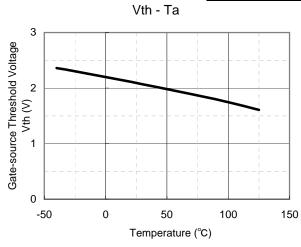


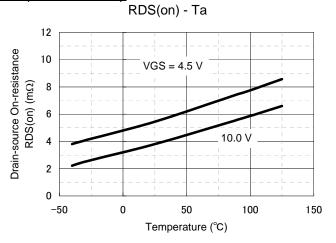
MOS FET FK8V03020L

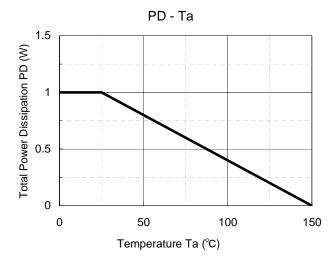


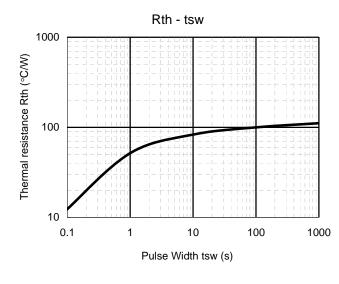
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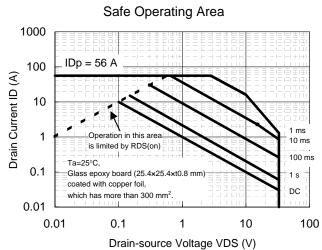
## Technical Data (reference)







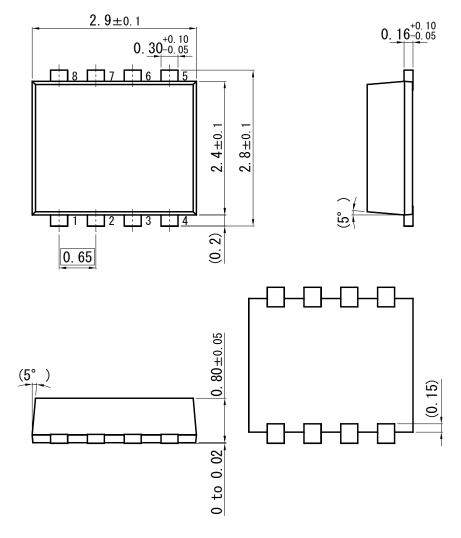




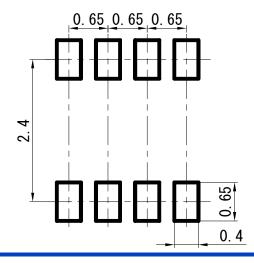
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WMini8-F1

Unit: mm



■ Land Pattern (Reference) (Unit : mm)



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